

## Automotive MOSFET

## OptiMOS™-5 Power-Transistor

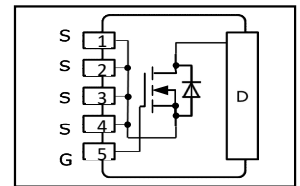
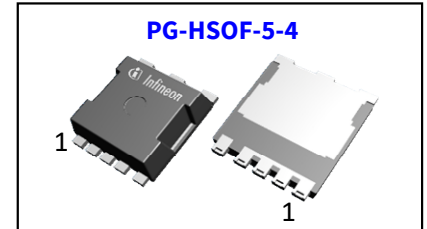


## Features

- OptiMOS™ power MOSFET for automotive applications
- N-channel – Enhancement mode – Normal Level
- Extended qualification beyond AEC-Q101
- Enhanced electrical testing
- Robust design
- MSL3 up to 260°C peak reflow
- 175°C operating temperature
- Green product (RoHS compliant)
- 100% Avalanche tested

## Potential applications

General automotive applications.



## Product Summary

$V_{DS}$	100	V
$R_{DS(on)}$	2.4	mΩ
$I_D$ (chip limited)	210	A

Type	Package	Marking
IAUA210N10S5N024	PG-HSOF-5-4	5N10024



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## Maximum ratings

at  $T_j=25\text{ °C}$ , unless otherwise specified

Parameter	Symbol	Conditions	Value	Unit
Continuous drain current	$I_D$	$V_{GS}=10\text{ V}$ , Chip limitation <sup>1)</sup>	210	A
		$V_{GS}=10\text{ V}$ , DC current <sup>2)</sup>	210	
		$T_a=85\text{ °C}$ , $V_{GS}=10\text{ V}$ , $R_{thJA}$ on 2s2p <sup>2,3)</sup>	26	
Pulsed drain current <sup>2)</sup>	$I_{D,pulse}$	$T_C=25\text{ °C}$ , $t_p=100\text{ }\mu\text{s}$	674	
Avalanche energy, single pulse <sup>2)</sup>	$E_{AS}$	$I_D=105\text{ A}$	245	mJ
Avalanche current, single pulse	$I_{AS}$	-	170	A
Gate source voltage	$V_{GS}$	-	$\pm 20$	V
Power dissipation	$P_{tot}$	$T_C=25\text{ °C}$	238	W
Operating and storage temperature	$T_j, T_{stg}$	-	-55 ... +175	°C
IEC climatic category; DIN IEC 68-1	-	-	55/175/56	

## Thermal characteristics<sup>2)</sup>

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	
Thermal resistance, junction - case	$R_{thJC}$	-	-	-	0.63	K/W
Thermal resistance, junction - ambient <sup>3)</sup>	$R_{thJA}$	-	-	22.7	-	

## Electrical characteristics

at  $T_j=25\text{ °C}$ , unless otherwise specified

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	

### Static characteristics

Drain-source breakdown voltage	$V_{(BR)DSS}$	$V_{GS}=0\text{ V}, I_D=1\text{ mA}$	100	-	-	V
Gate threshold voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=150\text{ }\mu\text{A}$	2.2	3	3.8	
Zero gate voltage drain current	$I_{DSS}$	$V_{DS}=100\text{ V}, V_{GS}=0\text{ V}, T_j=25\text{ °C}$	-	0.1	1	$\mu\text{A}$
		$V_{DS}=100\text{ V}, V_{GS}=0\text{ V}, T_j=100\text{ °C}^{2)}$	-	1	100	
Gate-source leakage current	$I_{GSS}$	$V_{GS}=20\text{ V}, V_{DS}=0\text{ V}$	-	-	100	nA
Drain-source on-state resistance	$R_{DS(on)}$	$V_{GS}=6\text{ V}, I_D=50\text{ A}$	-	2.5	3.0	m $\Omega$
		$V_{GS}=10\text{ V}, I_D=100\text{ A}$	-	2.0	2.4	
Gate resistance <sup>2)</sup>	$R_G$	-	-	1.4	-	$\Omega$

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	

**Dynamic characteristics<sup>2)</sup>**

Input capacitance	$C_{iss}$	$V_{GS}=0\text{ V}, V_{DS}=50\text{ V}, f=1\text{ MHz}$	-	6689	8696	pF
Output capacitance	$C_{oss}$		-	1073	1395	
Reverse transfer capacitance	$C_{rss}$		-	41	62	
Turn-on delay time	$t_{d(on)}$	$V_{DD}=50\text{ V}, V_{GS}=10\text{ V},$ $I_D=100\text{ A}, R_G=3.5\ \Omega$	-	16	-	ns
Rise time	$t_r$		-	8	-	
Turn-off delay time	$t_{d(off)}$		-	32	-	
Fall time	$t_f$		-	19	-	

**Gate Charge Characteristics<sup>2)</sup>**

Gate to source charge	$Q_{gs}$	$V_{DD}=50\text{ V}, I_D=100\text{ A},$ $V_{GS}=0\text{ to }10\text{ V}$	-	31	41	nC
Gate to drain charge	$Q_{gd}$		-	18	27	
Gate charge total	$Q_g$		-	91	119	
Gate plateau voltage	$V_{plateau}$		-	4.7	-	V

**Reverse Diode**

Diode continuous forward current <sup>2)</sup>	$I_S$	$T_C=25\text{ °C}$	-	-	210	A
Diode pulse current <sup>2)</sup>	$I_{S,pulse}$	$T_C=25\text{ °C}, t_p=100\ \mu\text{s}$	-	-	674	
Diode forward voltage	$V_{SD}$	$V_{GS}=0\text{ V}, I_F=100\text{ A},$ $T_j=25\text{ °C}$	-	0.9	1.2	V
Reverse recovery time <sup>2)</sup>	$t_{rr}$	$V_R=50\text{ V}, I_F=50\text{ A},$ $di_f/dt=100\text{ A}/\mu\text{s}$	-	63	-	ns
Reverse recovery charge <sup>2)</sup>	$Q_{rr}$		-	104	-	nC

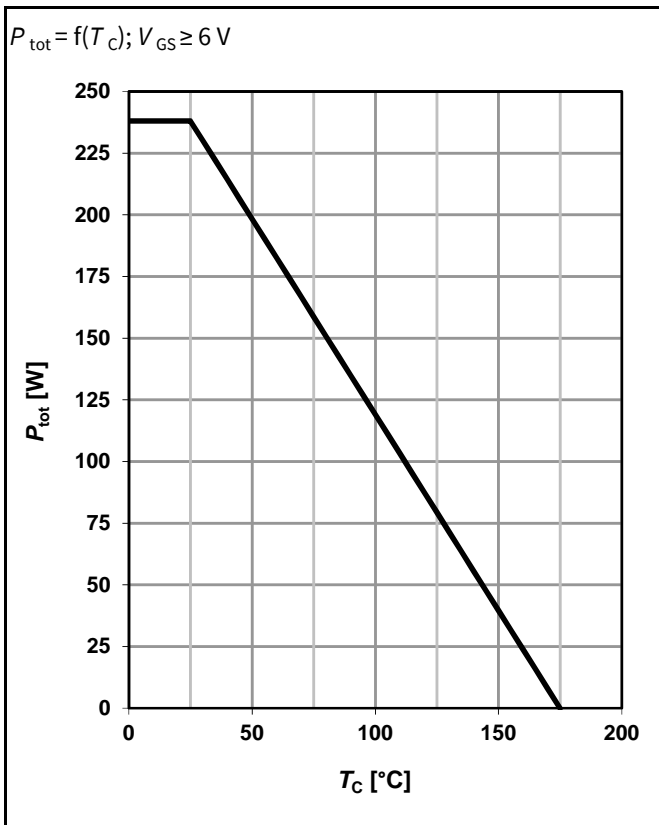
<sup>1)</sup> Practically the current is limited by the overall system design including the customer-specific PCB.

<sup>2)</sup> The parameter is not subject to production testing – specified by design.

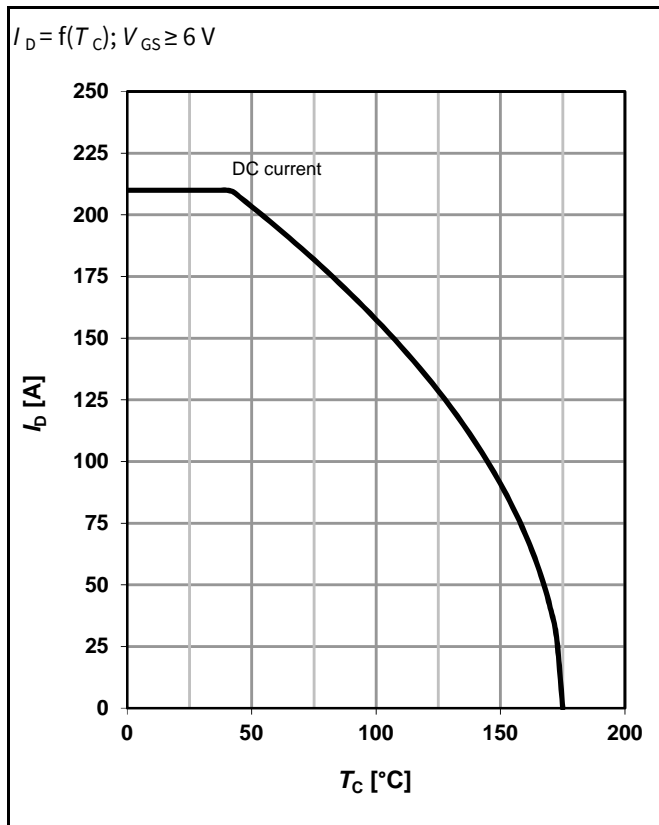
<sup>3)</sup> Device on 2s2p FR4 PCB defined in accordance with JEDEC standards (JESD51-5, -7). PCB is vertical in still air.

### Electrical characteristics diagrams

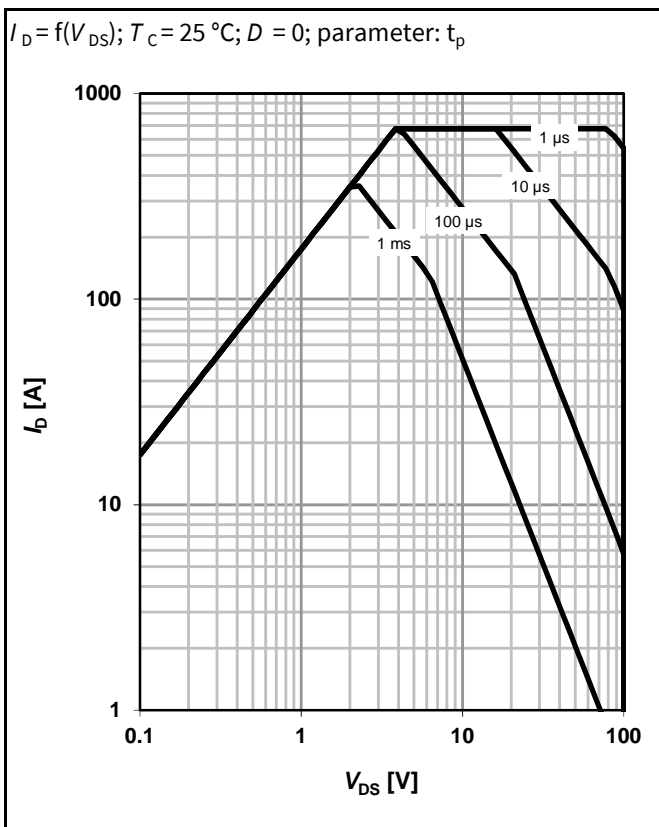
#### 1 Power dissipation



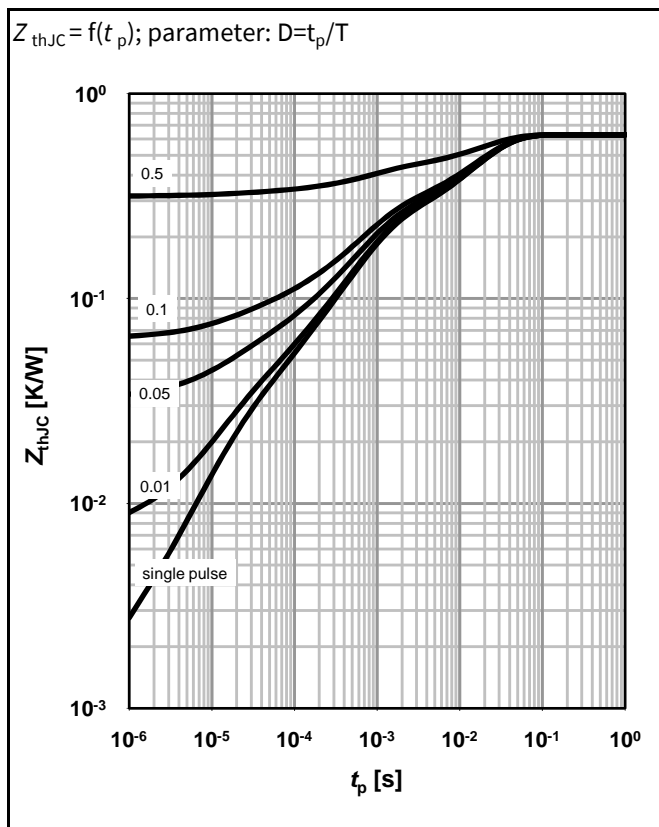
#### 2 Drain current



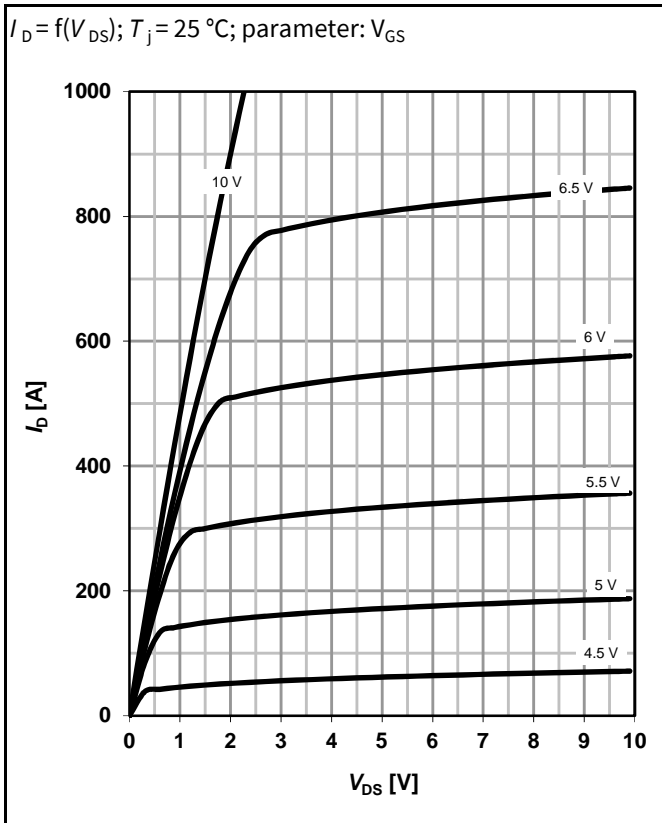
#### 3 Safe operating area



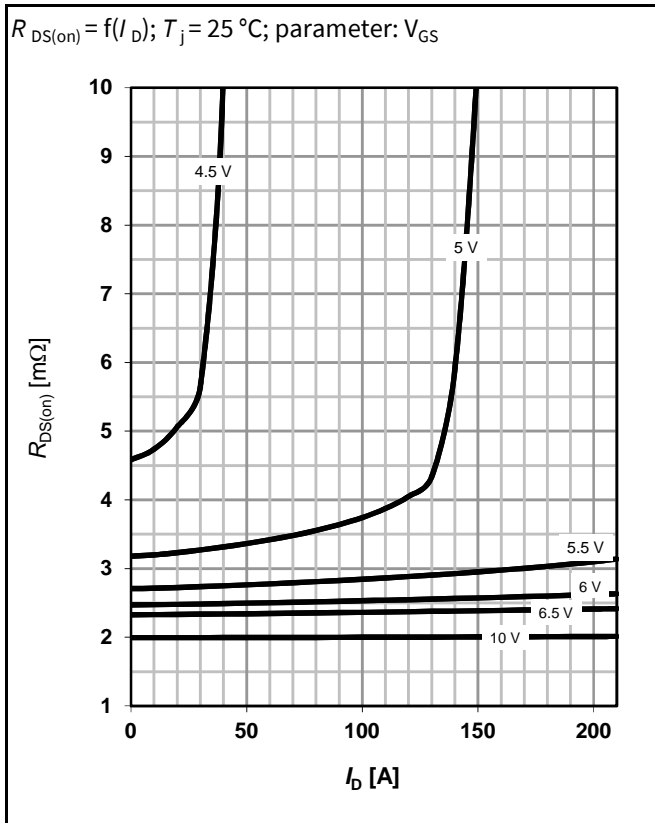
#### 4 Max. transient thermal impedance



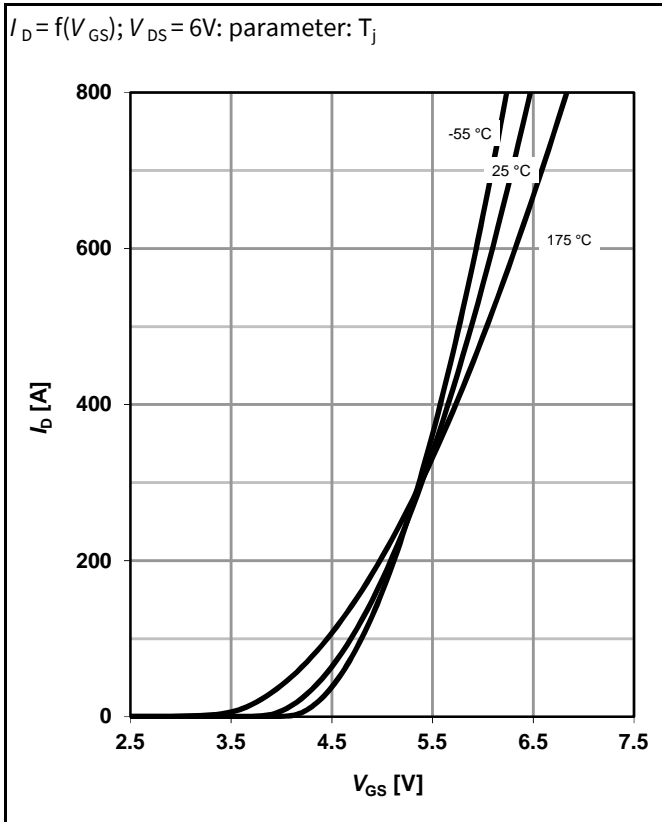
5 Typ. output characteristics



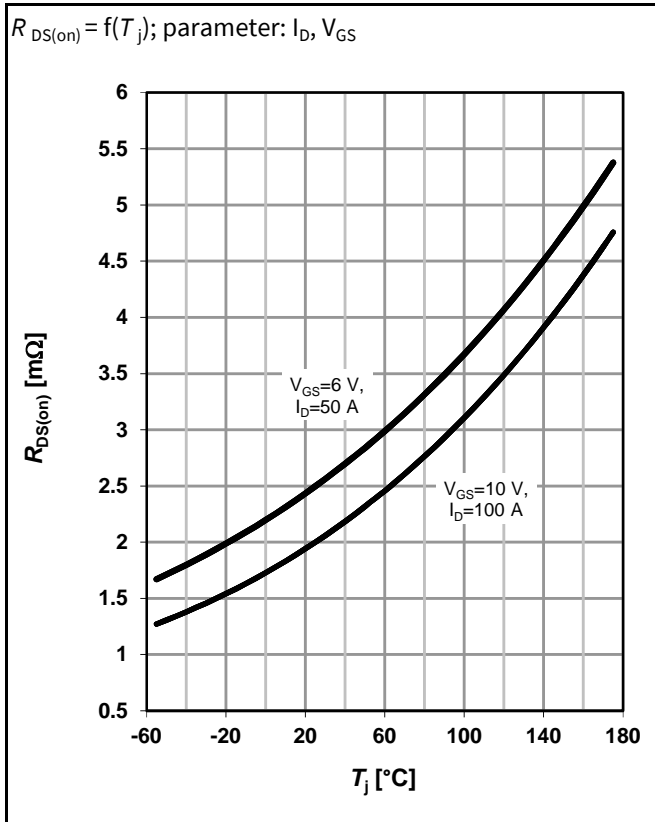
6 Typ. drain-source on-state resistance



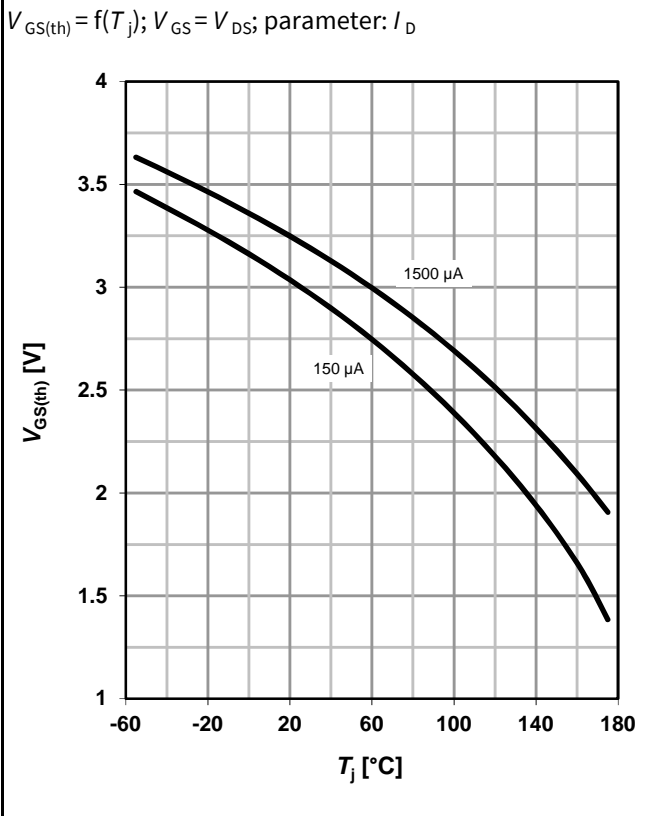
7 Typ. transfer characteristics



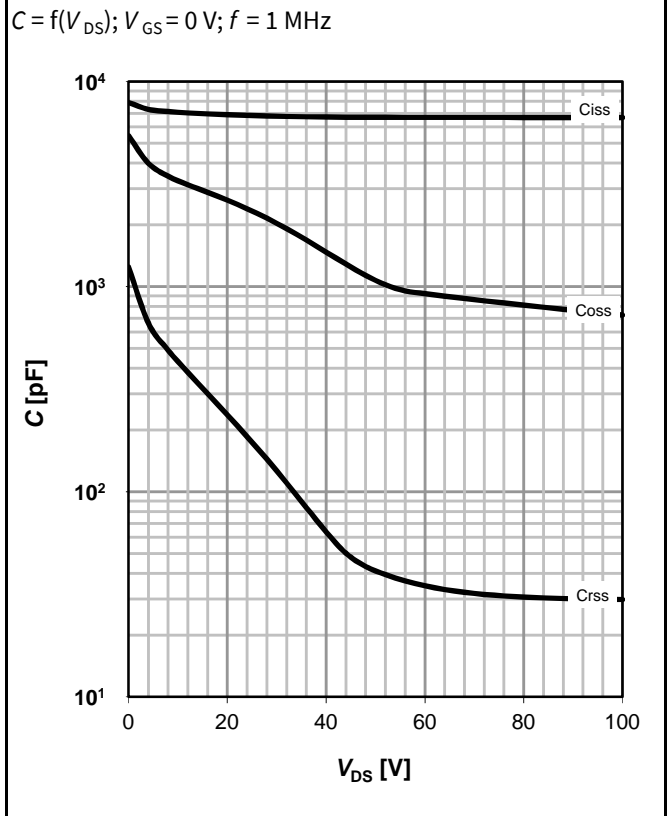
8 Typ. drain-source on-state resistance



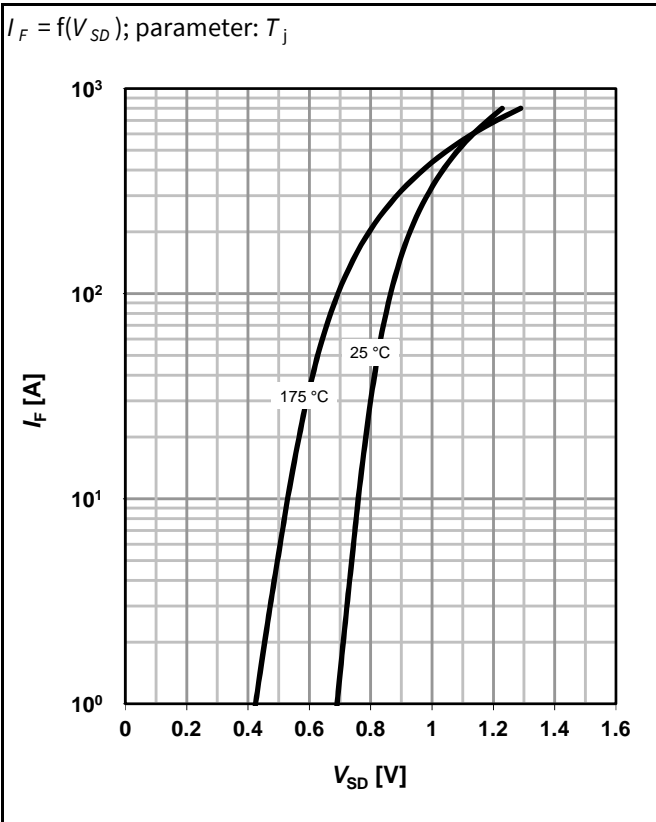
9 Typ. gate threshold voltage



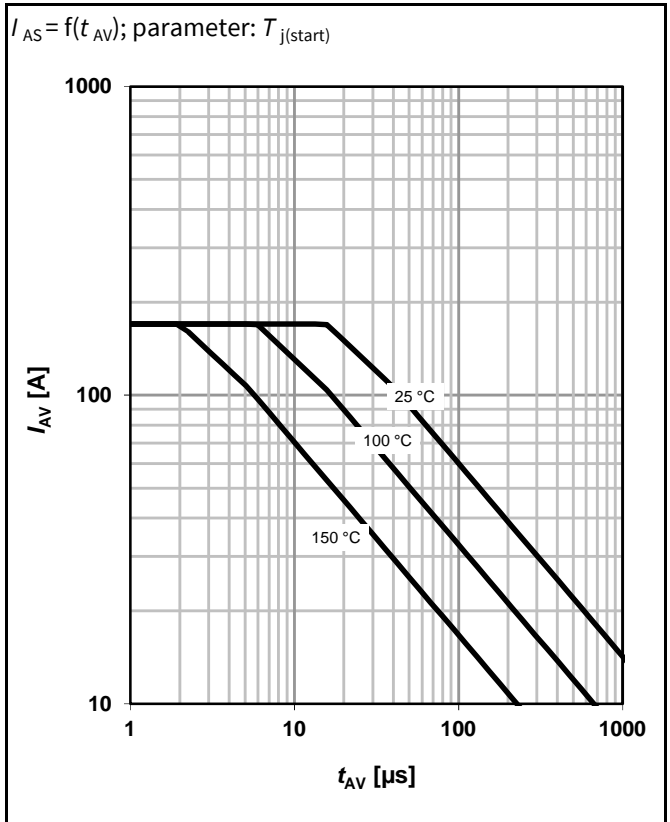
10 Typ. capacitances



11 Typical forward diode characteristics



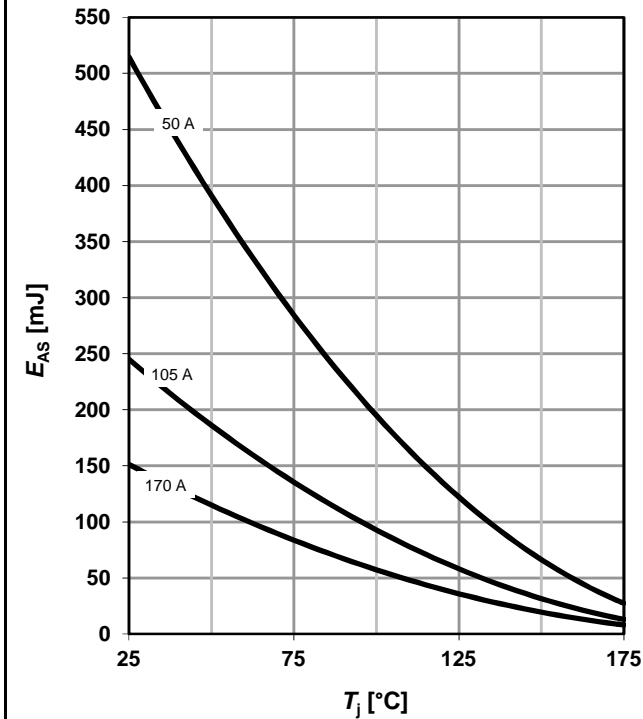
12 Typ. avalanche characteristics





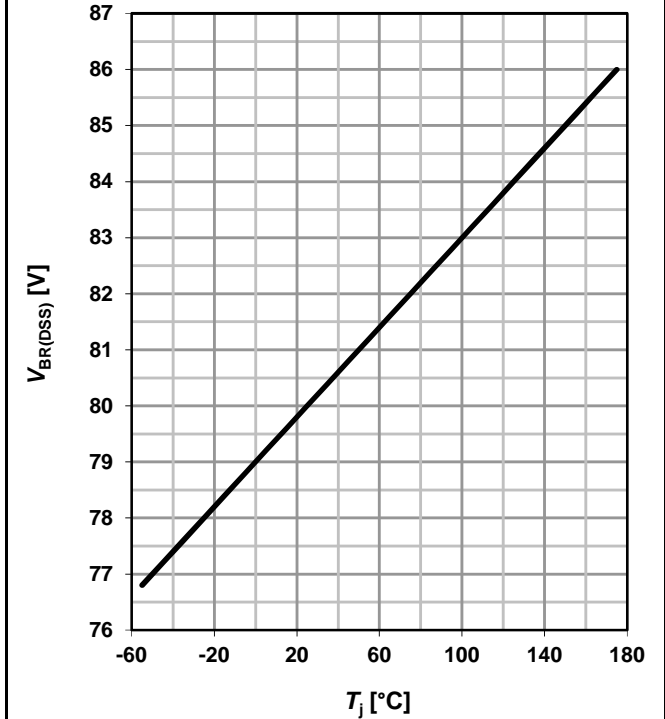
13 Typical avalanche energy

$E_{AS} = f(T_j)$ ; parameter: ID



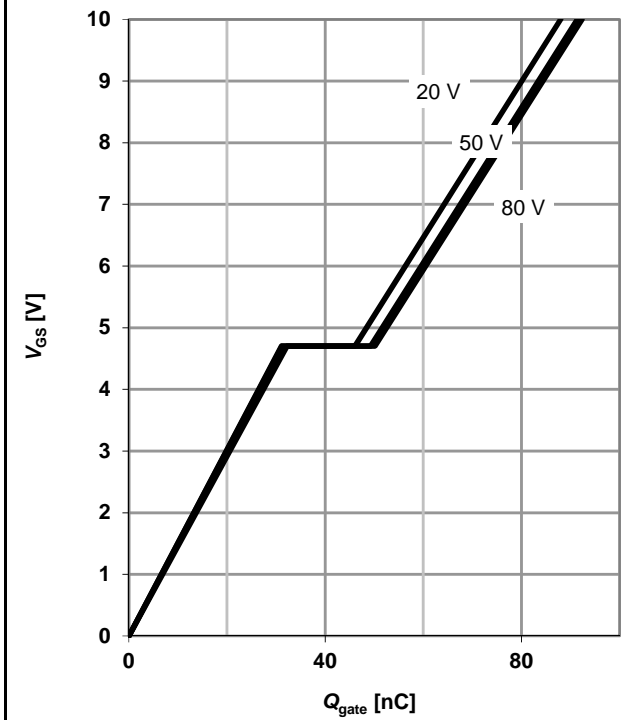
14 Drain-source breakdown voltage

$V_{BR(DSS)} = f(T_j)$ ;  $I_{D\_typ} = 1$  mA

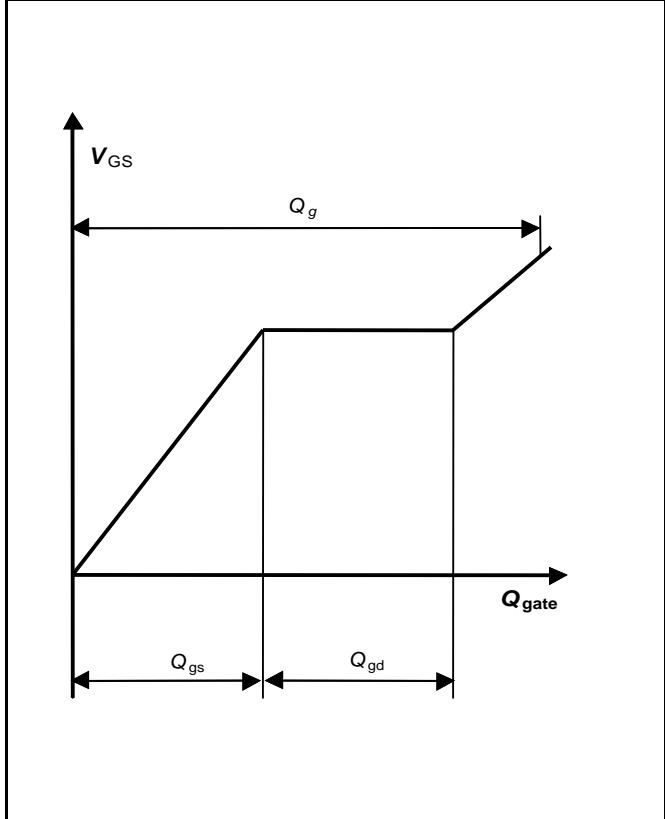


15 Typ. gate charge

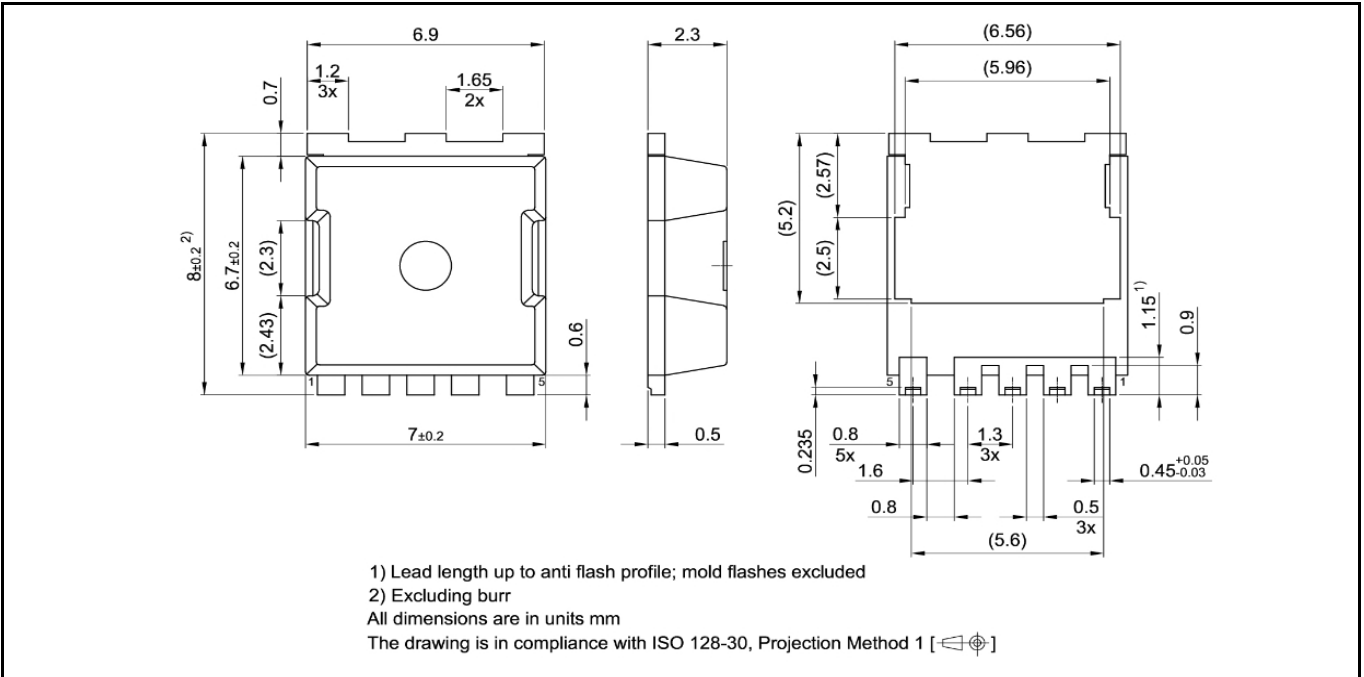
$V_{GS} = f(Q_{gate})$ ;  $I_D = 100$  A pulsed; parameter:  $V_{DD}$



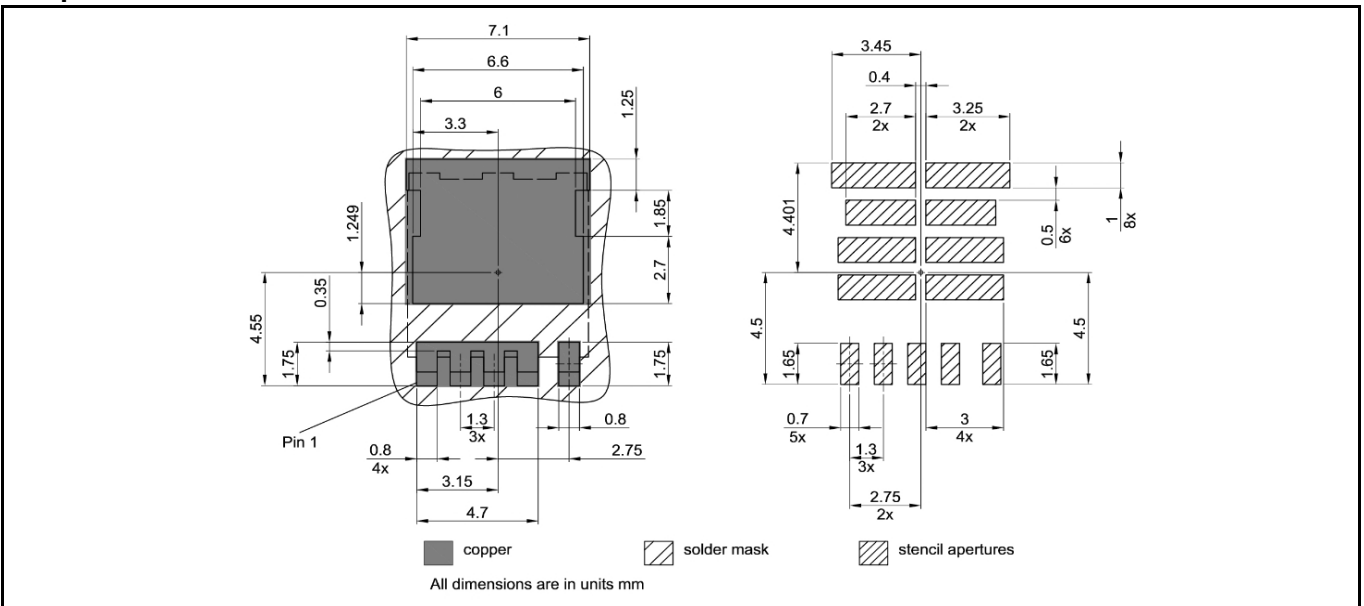
16 Gate charge waveforms



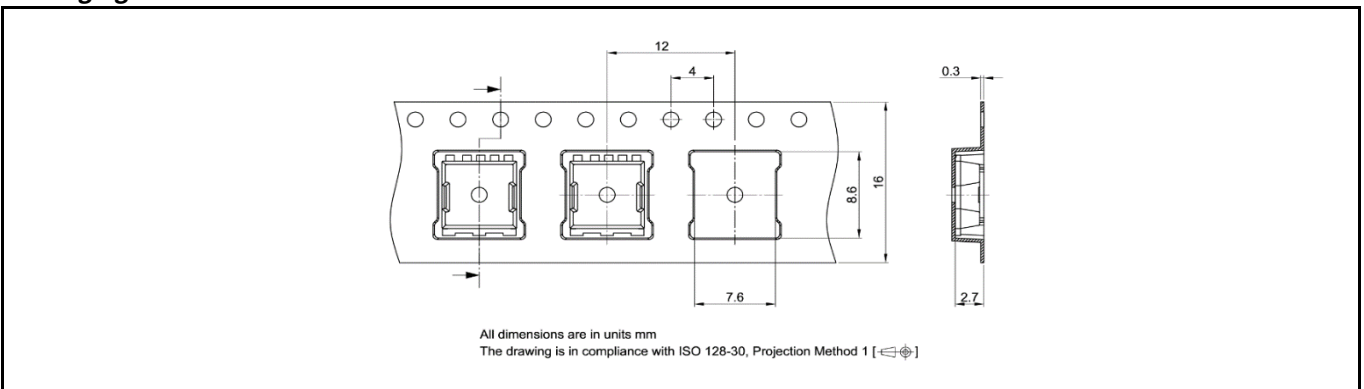
## Package Outline



## Footprint



## Packaging



## Revision History

Revision	Date	Changes
Revision 1.0	17.03.2021	Final Datasheet

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